

F1
cont

an interlayer insulating film located on the semiconductor substrate;

wirings located on the interlayer insulating film; and

a passivation film covering the surface of the interlayer insulating film and the wirings, including a first insulating film that is a modified Spin-on-Glass (SOG) film of an organic SOG film, wherein the modified SOG film contains boron impurity.

5

F2
sub G1

28. The semiconductor device according to Claim 25, wherein

the first insulating film contains the boron impurity to decompose organic components of the organic SOG film.

F3
sub G1

31. A semiconductor device comprising:

a semiconductor substrate;

an interlayer insulating film located on the semiconductor substrate;

wirings located on the interlayer insulating film; and

a passivation film covering the surface of the interlayer insulating film and the wirings, including a first insulating film that is a modified Spin-on-Glass (SOG) film of an inorganic SOG film, wherein the modified SOG film contains boron impurity.

5